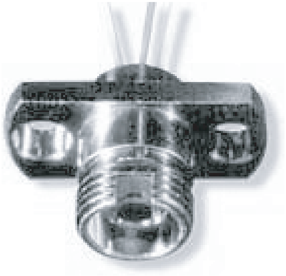
High Speed InGaAs p-i-n Photodiode

Sheet 1 of 1

13PD75-ST, -SMA, -FC, -SC

The 13PD75-ST, an InGaAs photodiode with a 75µm-diameter photosensitive region packaged in a TO-46 header and aligned in an AT&T ST active device mount, is intended for high speed and low noise applications. Planar semiconductor design and dielectric passivation provide superior low noise performance. Reliability is assured by hermetic sealing and 100% purge burn-in (200°C, 15 hours, Vr = 20V). The ST receptacle is suitable for bulkhead and PC Board mounting.



Features:

- Planar Structure
- Dielectric Passivation
- 100% Purge Burn-in
- High Responsivity

DEVICE CHARACTERISTICS

Parameters	Test Conditions	Minimum	Typical	Maximum	Units
Operating Voltage				–20	Volts
Dark Current	–5V		0.2	2	nA
Capacitance	–5V		0.7	0.9	pF
Responsivity	1300nm	0.65	0.8		A/W
Rise/Fall				0.5	ns
Frequency Response	(–3dB)		1.5		GHz

ABSOLUTE MAXIMUM RATINGS

Reverse Voltage	30 Volts
Forward Current	5mA
Reverse Current	5mA
Operating Temperature	–40°C to +85°C
Storage Temperature	–40°C to +85°C
Soldering Temperature	250°C

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